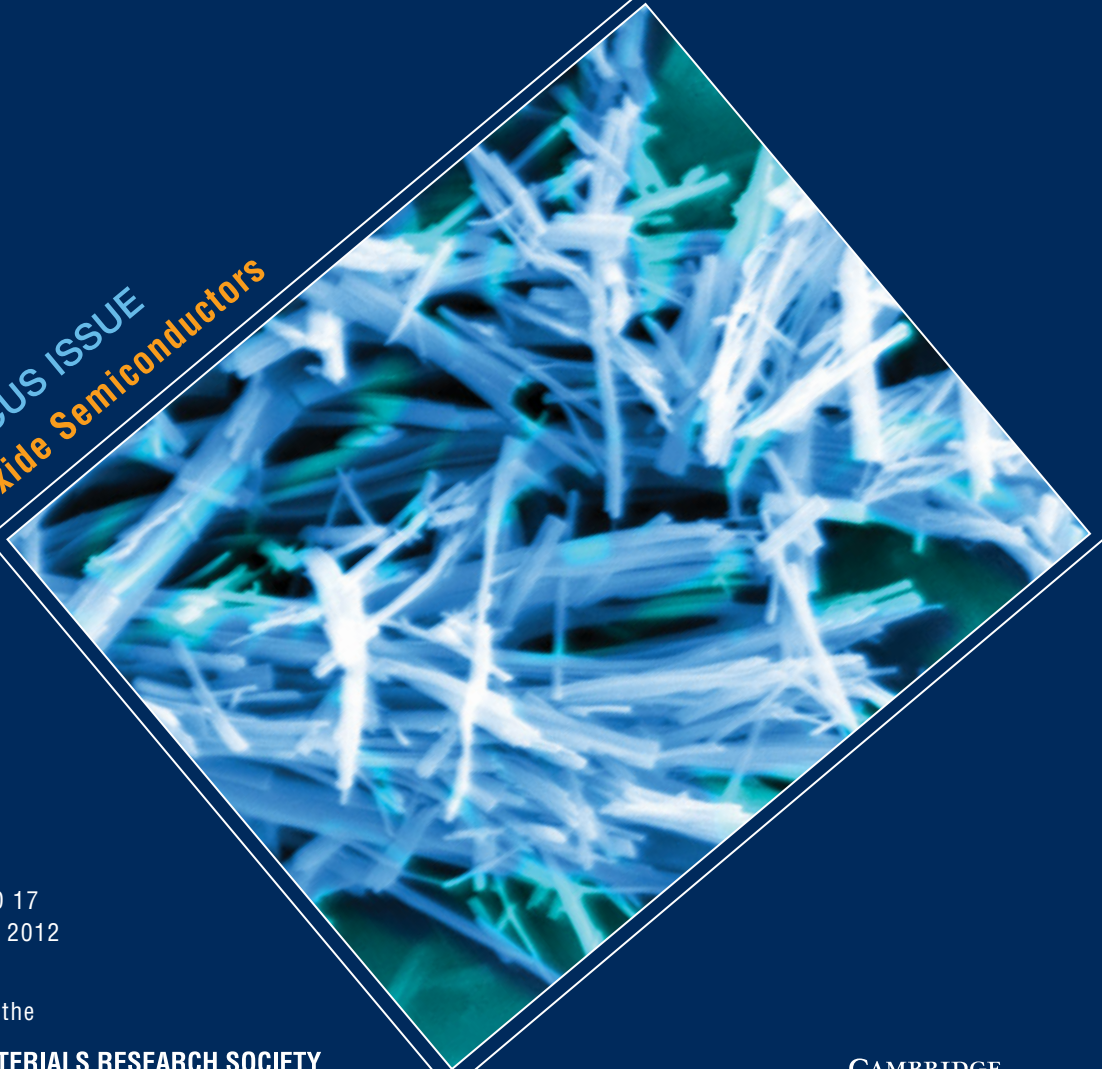




Journal of  
MATERIALS RESEARCH

FOCUS ISSUE  
Oxide Semiconductors



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Cover: SEM image of TiO<sub>2</sub> nanostructures ( $V_T = 20$  mL). [C. Liu and X. Wang: Mesoporous titanium dioxide nanobelts: Synthesis, morphology evolution and photocatalytic properties. p. 2265.]

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